



ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089

1N4933 thru 1N4937 Silicon Rectifier General Purpose, Fast Recovery DO-41 Type Package

Features:

- Fast Switching for High Efficiency
- Low Forward Voltage Drop
- Low Leakage Current
- High Forward Surge Capability

Maximum Ratings and Electrical Characteristics: ($T_A = +25^{\circ}\text{C}$ unless otherwise specified)

Maximum Repetitive Peak Reverse Voltage, V_{RRM}

1N4933	50V
1N4934	100V
1N4935	200V
1N4936	400V
1N4937	600V

Maximum RMS Voltage, V_{RMS}

1N4933	35V
1N4934	70V
1N4935	145V
1N4936	280V
1N4937	420V

Maximum DC Blocking Voltage, V_{DC}

1N4933	50V
1N4934	100V
1N4935	200V
1N4936	400V
1N4937	600V

Maximum Average Forward Rectified Current, $I_{F(AV)}$

.375" (9.5mm) Lead Length at $T_A = +75^{\circ}\text{C}$	1A
--	----

Peak Forward Surge Current, I_{FSM}

8.3ms Single Half Sine-Wave Superimposed on Rated Load	30A
--	-----

Maximum Reverse Recovery Current, I_{RM}

	2A
--	----

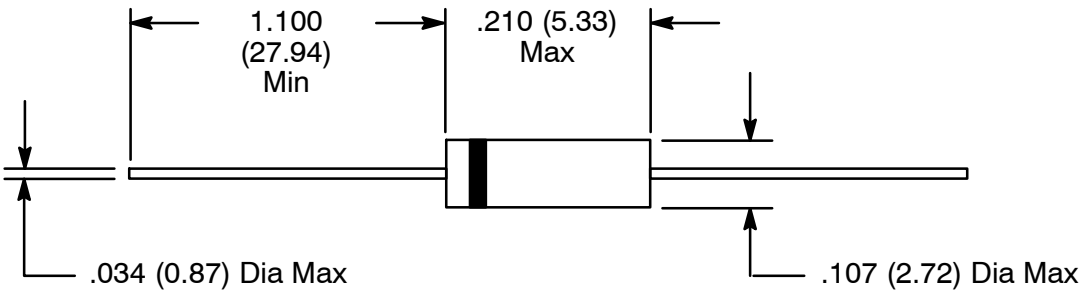
Maximum Instantaneous Forward Voltage at 1A DC, V_F

	1.2V
--	------

Maximum Ratings and Electrical Characteristics (Cont'd): ($T_A = +25^{\circ}\text{C}$ unless otherwise specified)

Maximum DC Reverse Current at Rated DC Blocking Voltage, I_R	
$T_A = +25^{\circ}\text{C}$	5 μA
$T_A = +100^{\circ}\text{C}$	100 μA
Maximum Reverse Recovery Time ($I_F = 1\text{A}$, $V_R = 30\text{V}$, $di/dt = 50\text{A}/\mu\text{s}$, $I_{rr} = 10\% I_{RM}$), t_{rr} ...	200ns
Typical Junction Capacitance (4V, 1MHz), C_J	12pF
Operating Junction Temperature Range, T_J	-50° to $+150^{\circ}\text{C}$
Storage Temperature Range, T_{stg}	-50° to $+150^{\circ}\text{C}$
Typical Thermal Resistance, Junction-to-Ambient (Note 1), R_{thJA}	$+55^{\circ}\text{C}/\text{W}$
Typical Thermal Resistance, Junction-to-Lead (Note 1), R_{thJL}	$+25^{\circ}\text{C}/\text{W}$

Note 1. Measured at .375" (9.5mm) lead length, PCB mounted.



Color Band Denotes Cathode